

Docket No.: MUH-12838

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By: 

Date: February 9, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 10/698,082  
Applicant : Armin Willmeroth et al.  
Filed : October 30, 2003  
Title : IGBT with Monolithic Integrated Antiparallel Diode  
Art Unit : to be assigned  
Examiner : to be assigned  
Customer No. : 24131

### INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner for Patents

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

Hajime Akiyama et al.: "Effects of Shorted Collector on Characteristics of IGBTs", *Proceedings of 1990 International Symposium on Power Semiconductor Devices and ICs, Tokyo, 1990, pp. 131-136.*

Respectfully submitted,

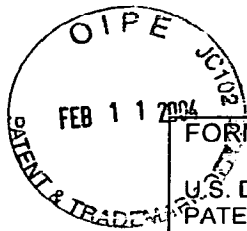


For Applicants

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<b>FORM PTO-1449 (SUBSTITUTE)</b> U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (37 CFR 1.98(b))				Attorney Docket No.:      Applic. No. <b>MUH-12838</b> <b>10/698,082</b>  Applicant <b>Armin Willmeroth et al.</b>  Filing Date                      Group Art Unit <b>October 30, 2003</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						
<b>FOREIGN PATENT DOCUMENT</b>							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J						
	K						
	L						
	M						
	N						
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
	O	Hajime Akiyama et al.: "Effects of Shorted Collector on Characteristics of IGBTs", <i>Proceedings of 1990 International Symposium on Power Semiconductor Devices and ICs, Tokyo, 1990, pp. 131-136</i>					
	P						
EXAMINER				DATE CONSIDERED			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							